Automotive ±70 V Fault-Protected LIN Transceiver with WAKE and INH

Features

- Compliant with LIN 2.0, LIN 2.1, LIN 2.2, LIN 2.2A and ISO 17987-4 Electrical Physical Layer (EPL) Specification
- Compliant with SAE J2602 LIN Network for Vehicle Applications
- Extended Bus Fault Protection and Common Mode Voltage for Automotive 48 V Battery Applications
- Support LIN Transmit Data Rates up to 20 kbps
- Support LIN Receive Data Rates up to 100 kbps
- Wide V_{BAT} Input Voltage Range Supports 4.5 V to 60 V
- Low-current Standby Mode and Sleep Mode with Bus Wake-up and Local Wake-up Capability
- Input Levels Compatible with 3.3-V and 5-V MCU Interface
- System-level Power Control with INH Pin
- Ideal Passive Behavior to LIN Bus when Unpowered
- Integrated Pull-up Resistor for LIN Slave Applications
- Protection Features:
  - Bus Pin IEC 61000-4-2 ESD Protection ±8 kV
  - Bus Fault Tolerant: ±70 V
  - V_{BAT} Undervoltage Protection
  - TXD Dominant Time-out Function
  - Thermal Shutdown Protection
- Available in SOP8 Package and Leadless DFN3X3-8 Package with Improved Automated Optical Inspection (AOI) Capability
- AEC-Q100 Qualified for Automotive Applications, Grade 1

Applications

- Automotive 48 V Battery Applications
- Automotive and Transportation
- Body Electronics / Lighting
- Power Train / Chassis
- Infotainment / Cluster
- ADAS / Safety

Description

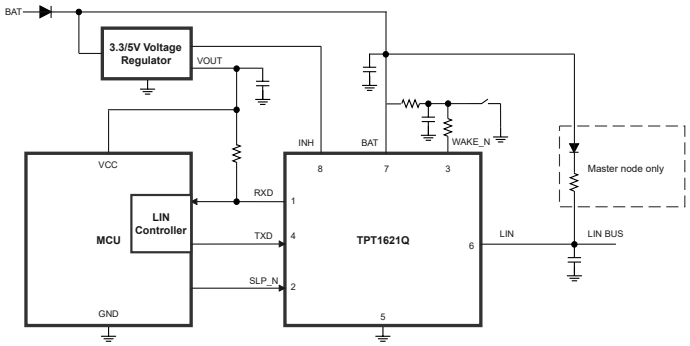
The TPT1621Q is a local interconnect network (LIN) physical layer transceiver that is compliant with ISO 17987-4, SAE J2602 and LIN 2.0, LIN 2.1, LIN 2.2, and LIN 2.2A physical layer standards. LIN is a low-speed universal asynchronous receiver transmitter (UART) communication protocol that supports automotive in-vehicle sub-networks.

The device supports LIN transmitter data rates up to 20 kbps and receiver data rates up to 100 kbps, with an enhanced timing margin. The device converts the transmitted data received at the TXD with the optimized slew rate to minimize the electromagnetic emission (EME) and reports the state of the LIN bus at the RXD.

As designed, the device has low-current standby and sleep modes with LIN BUS wake-up and local wake-up capability via the WAKE_N pin. The INH pin of the device is used to control voltage regulation to reduce system-level power consumption. For a master application, an external resistor in series with a diode should be connected between pin INH or pin VBAT and pin LIN. The device integrates a pull-up resistor for LIN slave applications and ESD protection which allows applications to operate with a reduced dependence on external components. Additionally, all devices include many protection features to enhance the device and network robustness.

The TPT1621Q is available in SOP8 and DFN3X3-8 packages and is AEC-Q100 qualified for automotive applications.

Typical Application Circuit



Automotive ±70 V Fault-Protected LIN Transceiver with WAKE and INH

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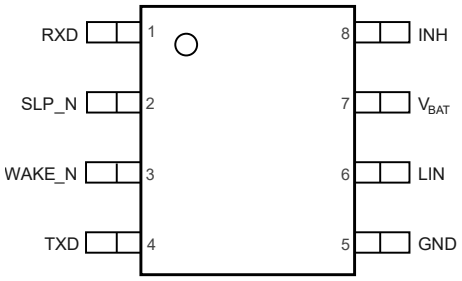
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Revision History

Date	Revision	Notes
2026-08-20	Rev.A.0	Released version

Pin Configuration and Functions

TPT1621Q
SOP8 Package
Top View



TPT1621Q
DFN3X3-8 Package
Top View

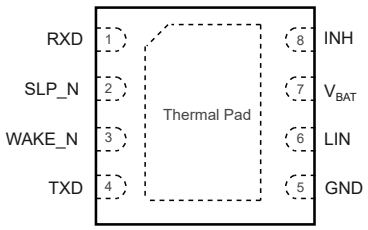


Table 1. Pin Functions: TPT1621Q

Pin		I/O	Description
No.	Name		
1	RXD	Output	LIN receives data output
2	SLP_N	Input	Sleep mode control input, active low
3	WAKE_N	HV Input	Local wake-up Input, active low
4	TXD	Input	LIN transmits data input
5	GND	GND	Ground
6	LIN	BUS I/O	LIN Bus input/output line
7	VBAT	Power	High-voltage power supply from the battery
8	INH	HV Output	Inhibit output to control external voltage regulators
	Thermal pad	GND	Thermal pad of DFN package, required to connect the exposed pad to Ground

Specifications

Absolute Maximum Ratings (1)

Parameter		Conditions	Min	Max	Unit
V_{BAT}	Battery Supply Voltage Range		−0.3	70	V
V_{TXD}	Pin TXD Voltage Range		−0.3	7	V
V_{RXD}	Pin RXD Voltage Range		−0.3	7	V
V_{SLP_N}	Pin SLP_N Voltage Range		−0.3	7	V
V_{WAKE_N}	Pin WAKE_N Voltage Range		−0.3	70	V
V_{INH}	Pin INH Voltage Range		−0.3	70	V
V_{LIN}	Pin LIN Voltage Range	With respect to GND	−70	70	V
T_J	Junction Temperature		−40	150	°C
T_{STG}	Storage Temperature		−55	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

ESD (Electrostatic Discharge Protection)

Parameter		Condition	Min	Max	Unit
V_{ESD}	Electrostatic Discharge	IEC61000-4-2 (150 pF, 330 Ω discharge circuit), contact discharge on LIN, WAKE_N pins	−8	8	kV
		Human Body Model (HBM) on LIN, WAKE_N pins	−10	10	kV
		Human Body Model (HBM) on any other pins	−7	7	kV
		Charged Device Model (CDM) on all pins	−1.5	1.5	kV
V_{TRAN}	Transient Immunity ISO 7637-2 on Bus Pins	Pulse1	−100		V
		Pulse2a		75	V
		Pulse3a	−150		V
		Pulse3b		100	V

Recommended Operating Conditions

	Parameter	Min	Max	Unit
V_{BAT}	Battery Power Supply	4.5	60	V
V_{LIN}	LIN Bus Input Voltage	0	60	V
V_{WAKE_N}	WAKE_N Pin Input Voltage	0	60	V
V_{LOGIC}	Logic Pin Voltage	0	5.25	V
T_A	Operating Ambient Temperature	−40	125	°C

Thermal Information

Package Type	θ_{JA}	θ_{JB}	θ_{JC}	Unit
SOP8	126.3	98.3	69.4	°C/W
DFN3X3-8	42.2	7.6	56.4	°C/W

Electrical Characteristics

All test conditions: V_{BAT} = 4.5 V to 60 V, R_L = 500 Ω, T_A = −40°C to 125°C, typical values are tested at V_{BAT} = 12 V, unless otherwise noted.

Parameter		Conditions	Min	Typ	Max	Unit
Pin VBAT						
$V_{TH_VBAT_L}$	Low Level of VBAT UVLO Threshold Voltage		3.50	3.9		V
$V_{TH_VBAT_H}$	High Level of VBAT UVLO Threshold Voltage			4.1	4.45	V
V_{HYS_VBAT}	Hysteresis Voltage on Power-on Reset (1)			0.15		V
I_{BAT}	Sleep Mode Supply Current	V_{LIN} = V_{BAT}; V_{WAKE_N} = V_{BAT}; V_{TXD} = 0 V; V_{SLP_N} = 0 V		8	17	μA
	Standby Mode Supply Current	Recessive; V_{INH} = V_{LIN} = V_{WAKE_N} = V_{BAT} = 60 V; V_{TXD} = 5 V; V_{SLP_N} = 0 V		40	55	μA
		Dominant; V_{INH} = V_{WAKE_N} = V_{BAT} = 60 V; V_{LIN} = 0 V ; V_{TXD} = 0 V; V_{SLP_N} = 0 V		400	2200	μA
	Normal Mode Supply Current	Recessive; V_{INH} = V_{LIN} = V_{WAKE_N} = V_{BAT} = 60 V; V_{TXD} = 5 V; V_{SLP_N} = 5 V		230	450	μA
		Dominant; V_{BAT} = 60 V; V_{INH} = 60 V; V_{LIN} = 0 V; V_{WAKE_N} = 60 V; V_{TXD} = 0 V; V_{SLP_N} = 5 V		1.1	7.5	mA
Pin TXD						
V_{IH}	High-Level Input Voltage		2		7	V
V_{IL}	Low-Level Input Voltage		−0.3		0.8	V
V_{HYS_TXD}	Hysteresis Voltage on Pin TXD (1)			190		mV
R_{PD_TXD}	Pin TXD Pull-down Resistance	V_{TXD} = 5 V	150	500	1200	kΩ
I_{IL}	Low-Level Input Current	V_{TXD} = 0 V	−1		1	μA
I_{OL}	Low-Level Output Current	Local wake-up request; Standby mode; V_{WAKE_N} = 0 V; V_{LIN} = V_{BAT}; VTXD = 0.4 V	1.5			mA
Pin SLP_N						
V_{IH}	High-Level Input Voltage		2		7	V
V_{IL}	Low-Level Input Voltage		−0.3		0.8	V

Parameter		Conditions	Min	Typ	Max	Unit
$V_{HYS_SLP_N}$	Hysteresis Voltage on Pin SLP_N (1)			190		mV
$R_{PD_SLP_N}$	Pin SLP_N Pull-down Resistance	V_{SLP_N} = 5 V	150	500	1200	kΩ
I_{IL}	Low-Level Input Current	V_{SLP_N} = 0 V	−1		1	μA
Pin RXD						
I_{OL}	Low-Level Output Current	Normal mode; V_{LIN} = 0 V, V_{RXD} = 0.4 V	1.5	4	8	mA
I_{LH}	High-Level Leakage Current	Normal mode; V_{LIN} = V_{BAT}, V_{RXD} = 5 V	−1	0	1	μA
Pin WAKE_N						
V_{IL}	Low-Level Input Voltage		V_{BAT} − 3.3		V_{BAT} +0.3	V
I_{PU_L}	Low-Level Pull-up Current	V_{WAKE_N} = 0 V	−30	−11.6	−1	μA
I_{IH}	High-Level Leakage Current		−1	0	1	μA
Pin INH						
$R_{SW(VBAT-INH)}$	Switch-on resistance between pins V_{BAT} and INH	Standby; Normal and Power on modes; I_{INH} = −15 mA; V_{BAT} = 60 V		20	40	Ω
I_{LH}	High-Level Leakage Current	Sleep mode; V_{INH} = V_{BAT}	−1	0	1	μA
Pin LIN						
I_{BUS_LIM}	Dominant Output Current Limitation	V_{BAT} = V_{LIN} = 18 V; V_{TXD} = 0 V	90		200	mA
R_{PU}	Pull-up Resistance	Sleep mode; V_{SLP_N} = 0 V	50	180	250	kΩ
$I_{BUS_PAS_REC}$	Receiver Recessive Input Leakage Current	V_{BAT} = 5.5 V; V_{LIN} = 54 V; V_{TXD} = 5 V			5	μA
$I_{BUS_PAS_DOM}$	Receiver Dominant Input Leakage Current	Normal mode; V_{BAT} = 24 V; V_{LIN} = 0 V; V_{TXD} = 5 V	−1000			μA
$V_{SerDiode}$	Voltage Drop at the Serial Diode (1)	Pull-up path with R_{SLAVE}; $I_{SerDiode}$ = 10 μA	0.3		1	V
$I_{BUS_NO_GND}$	Ground Loss Bus Current	V_{BAT} = 54 V; V_{LIN} = 0 V	−1400		10	μA
$I_{BUS_NO_BAT}$	Battery Loss Bus Current	V_{BAT} = 0 V; V_{LIN} = 54 V			1	μA
V_{BUS_DOM}	Receiver Dominant				0.4 × V_{BAT}	V
V_{BUS_REC}	Receiver Recessive		0.6 × V_{BAT}			V
V_{BUS_CNT}	Receiver Center Voltage	5.5 V ≤ V_{BAT} ≤ 40 V	0.475 × V_{BAT}	0.5 × V_{BAT}	0.525 × V_{BAT}	V
V_{HYS}	Receiver Hysteresis Voltage				0.175 x V_{BAT}	V
R_{SLAVE}	Slave Resistance	Between LIN and V_{BAT};	20	30	47	kΩ

Parameter		Conditions	Min	Typ	Max	Unit
		V_{BAT} = 12 V; V_{LIN} = 0 V				
C_{LIN}	Pin LIN Capacitance (1)				30	pF
V_{O_REC}	Recessive Output Voltage	Normal mode; V_{TXD} = 5 V	0.85 × V_{BAT}			V
V_{O_DOM}	Dominant Output Voltage	Normal mode; V_{BAT} ≤ 7 V ; V_{TXD} = 0 V			1.4	V
		Normal mode; 7 V < V_{BAT} ≤ 54 V ; V_{TXD} = 0 V			0.2 × V_{BAT}	V
Temperature Detection						
T_{J_SD}	Thermal Shutdown Temperature (1)		150	180	200	°C
$T_{J_SD_HYS}$	Thermal Shutdown Junction Hysteresis (1)		10	45	65	°C

(1) The data is based on bench tests and design simulations.

Duty Cycles

All test conditions: V_{BAT} = 4.5 V to 60 V, R_L = 500 Ω, T_A = −40°C to 125°C, see Figure 2, unless otherwise noted.

Parameter		Conditions	Min	Typ	Max	Unit
D1	Duty cycle 1; D1 = $t_{BUS_REC_MIN}$ / (2 × t_{BIT}); 12 V LIN networks	$V_{TH_REC_MAX}$ = 0.744 × V_{BAT}; $V_{TH_DOM_MAX}$ = 0.581 × V_{BAT}; 20 kbps; t_{BIT} = 50 µs; 7 V ≤ V_{BAT} ≤ 18 V	0.396			
		$V_{TH_REC_MAX}$ = 0.655 × V_{BAT}; $V_{TH_DOM_MAX}$ = 0.499 × V_{BAT}; 20 kbps; t_{BIT} = 50 µs; 4.5 V ≤ V_{BAT} < 7 V(1)	0.396			
D1	Duty cycle 1; D1 = $t_{BUS_REC_MIN}$ / (2 × t_{BIT}); 24 V LIN networks	$V_{TH_REC_MAX}$ = 0.710 × V_{BAT}; $V_{TH_DOM_MAX}$ = 0.554 × V_{BAT}; 20 kbps; t_{BIT} = 50 µs; 15 V ≤ V_{BAT} ≤ 36 V	0.33			
D2	Duty cycle 2; D2 = $t_{BUS_REC_MAX}$ / (2 × t_{BIT}); 12 V LIN networks	$V_{TH_REC_MIN}$ = 0.422 × V_{BAT}; $V_{TH_DOM_MIN}$ = 0.284 × V_{BAT}; 20 kbps; t_{BIT} = 50 µs; 7 V ≤ V_{BAT} ≤ 18 V			0.581	
		$V_{TH_REC_MIN}$ = 0.496 × V_{BAT}; $V_{TH_DOM_MIN}$ = 0.361 × V_{BAT}; 20 kbps; t_{BIT} = 50 µs; 4.5 V ≤ V_{BAT} < 7 V (1)			0.581	
D2	Duty cycle 2; D2 = $t_{BUS_REC_MAX}$ / (2 × t_{BIT}); 24 V LIN networks	$V_{TH_REC_MIN}$ = 0.446 × V_{BAT}; $V_{TH_DOM_MIN}$ = 0.302 × V_{BAT}; 20 kbps; t_{BIT} = 50 µs; 15 V ≤ V_{BAT} ≤ 36 V			0.642	
D3	Duty cycle 3; D3 = $t_{BUS_REC_MIN}$ / (2 × t_{BIT}); 12 V LIN networks	$V_{TH_REC_MAX}$ = 0.778 × V_{BAT}; $V_{TH_DOM_MAX}$ = 0.616 × V_{BAT}; 10.4 kbps; t_{BIT} = 96 µs; 7 V ≤ V_{BAT} ≤ 18 V	0.417			
		$V_{TH_REC_MAX}$ = 0.665 × V_{BAT}; $V_{TH_DOM_MAX}$ = 0.499 × V_{BAT}; 10.4 kbps; t_{BIT} = 96 µs; 4.5 V ≤ V_{BAT}< 7 V (1)	0.417			
D3	Duty cycle 3; D3 = $t_{BUS_REC_MIN}$ / (2 × t_{BIT}); 24 V LIN networks	$V_{TH_REC_MAX}$ = 0.744 × V_{BAT}; $V_{TH_DOM_MAX}$ = 0.581 × V_{BAT}; 10.4 kbps; t_{BIT} = 96 µs; 7 V < V_{BAT} ≤ 36 V	0.386			
D4	Duty cycle 4; D4 = $t_{BUS_REC_MAX}$ / (2 × t_{BIT}); 12 V LIN networks	$V_{TH_REC_MIN}$ = 0.389 × V_{BAT}; $V_{TH_DOM_MIN}$ = 0.251 × V_{BAT}; 10.4 kbps; t_{BIT} = 96 µs;			0.590	

Parameter		Conditions	Min	Typ	Max	Unit
		7 V ≤ V_{BAT} ≤ 18 V				
		$V_{TH_REC_MIN}$ = 0.496 × V_{BAT}; $V_{TH_DOM_MIN}$ = 0.361 × V_{BAT}; 10.4 kbps; t_{BIT} = 96 µs; 4.5 V ≤ V_{BAT} < 7 V (1)			0.590	
D4	Duty cycle 4; D4 = $t_{BUS_REC_MAX}$ / (2 × t_{BIT}); 24 V LIN networks	$V_{TH_REC_MIN}$ = 0.422 × V_{BAT}; $V_{TH_DOM_MIN}$ = 0.284 × V_{BAT}; 10.4 kbps; t_{BIT} = 96 µs; 7.6 V < V_{BAT} ≤ 36 V			0.591	

AC Timing Requirements

All test conditions: V_{BAT} = 4.5 V to 60 V, R_L = 500 Ω, T_A = −40°C to 125°C, typical values are tested at V_{BAT} = 12 V, unless otherwise noted.

Parameter		Conditions	Min	Typ	Max	Unit
t_F	LIN Bus Fall Time	C_{BUS} = 1 nF, R_{BUS} = 1 kΩ; C_{BUS} = 6.8 nF, R_{BUS} = 660 Ω; C_{BUS} = 10 nF, R_{BUS} = 500 Ω;			22.5	μs
t_R	LIN Bus Rise Time	C_{BUS} = 1 nF, R_{BUS} = 1 kΩ; C_{BUS} = 6.8 nF, R_{BUS} = 660 Ω; C_{BUS} = 10 nF, R_{BUS} = 500 Ω;			22.5	μs
$\Delta t_{(R-F)}$	Difference between LIN Bus Rise-and-Fall Time		−7		7	μs
t_{TX_PD}	Transmitter Propagation Delay	Rising and falling			7	μs
t_{TX_SYM}	Transmitter Propagation Delay Symmetry		−5		5	μs
t_{RX_PD}	Receiver Propagation Delay	Rising and falling			6	μs
t_{RX_SYM}	Receiver Propagation Delay Symmetry		−2		2	μs
$t_{WAKE_DOM_LIN}$	LIN Dominant Wake-up Time	Sleep mode	30	80	150	μs
$t_{WAKE_DOM_WAKE_N}$	Pin WAKE_N Dominant Wake-up Time	Sleep mode	7	27.5	60	μs
$t_{GOTONORM}$	Go-to-Normal Time	Mode change time from Sleep, Power-on, Standby mode into Normal mode	2	6.1	10	μs
$t_{INITNORM}$	Normal Mode Initialization Time (1)		5	13.5	20	μs
$t_{GOTOSLEEP}$	Go-to-Sleep Time	Mode change time from Normal to Sleep mode	2	6.1	10	μs
$t_{TO_DOM_TXD}$	TXD dominant time-out time	V_{TXD} = 0 V	27	60	90	ms

(1) The data is based on bench tests and design simulations.

Parameter Measurement Information

Test Circuit

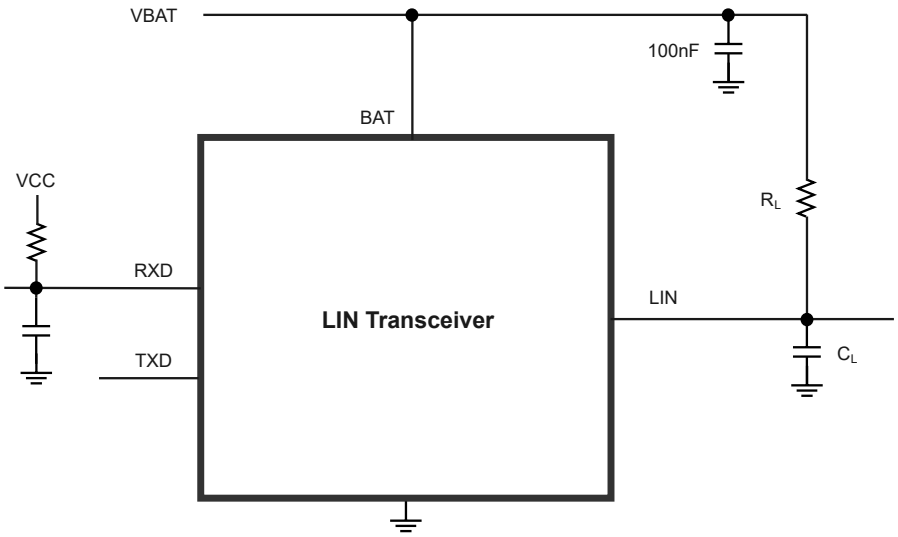


Figure 1. LIN Transceiver Timing Parameter Test Circuit

Parameter Diagram

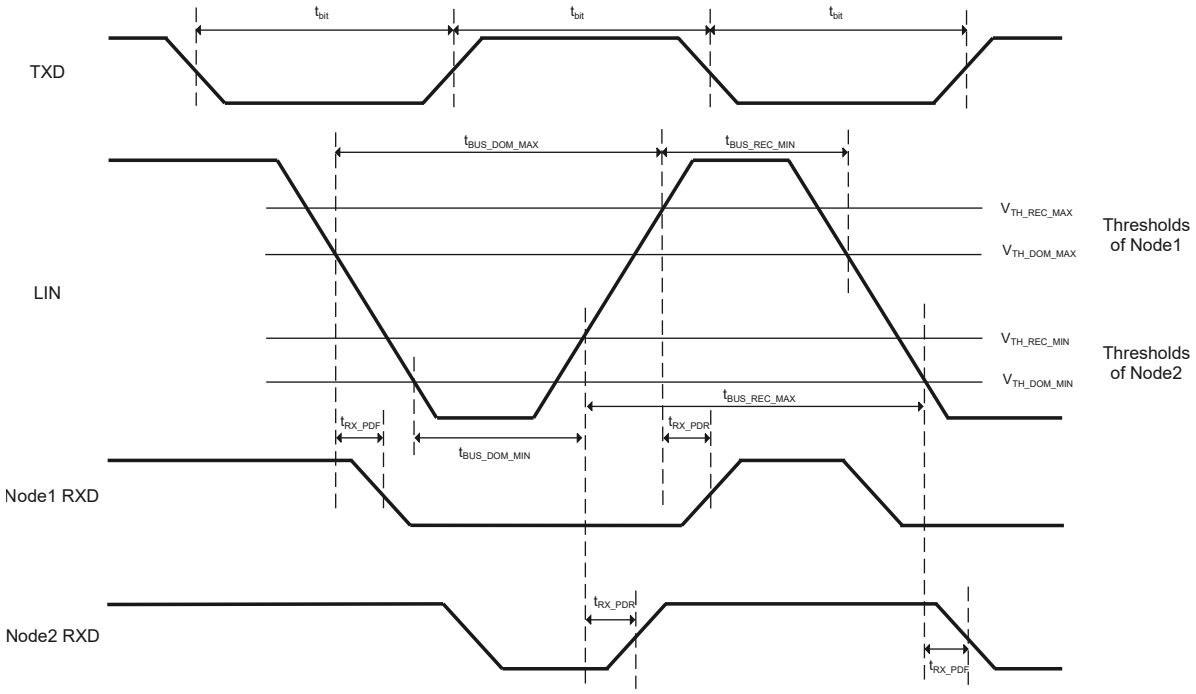


Figure 2. LIN Transceiver Timing Diagram

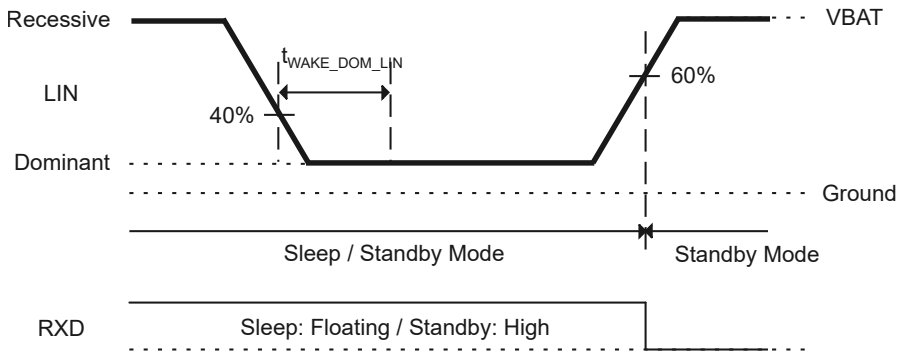


Figure 3. Remote Wake-up Diagram

Detailed Description

Overview

The TPT1621Q is a local interconnect network (LIN) physical layer transceiver that is compliant with ISO 17987-4, SAE J2602 and LIN 2.0, LIN 2.1, LIN 2.2, and LIN 2.2A physical layer standards. LIN is a low-speed universal asynchronous receiver transmitter (UART) communication protocol that supports automotive in-vehicle sub-networks. The device supports LIN transmitter data rates up to 20 kbps and receiver data rates up to 100 kbps, with an enhanced timing margin. The device converts the transmitted data received at the TXD with the optimized slew rate to minimize the electromagnetic emission (EME) and reports the state of the LIN bus at the RXD. As designed, the device features overvoltage and loss of ground protection from −70 V to +70 V, and over-temperature shutdown. The device has low-current standby and sleep modes with LIN BUS wake-up and local wake-up capability via the WAKE_N pin. The INH pin of the device is used to control voltage regulation to reduce system-level power consumption. The device integrates a pull-up resistor for LIN slave applications and ESD protection which allows applications to operate with a reduced dependence on external components. Additionally, all devices include many protection features to enhance the device and network robustness. The TPT1621Q is available in SOP8 and DFN3X3-8 packages and is AEC-Q100 qualified for automotive applications.

Functional Block Diagram

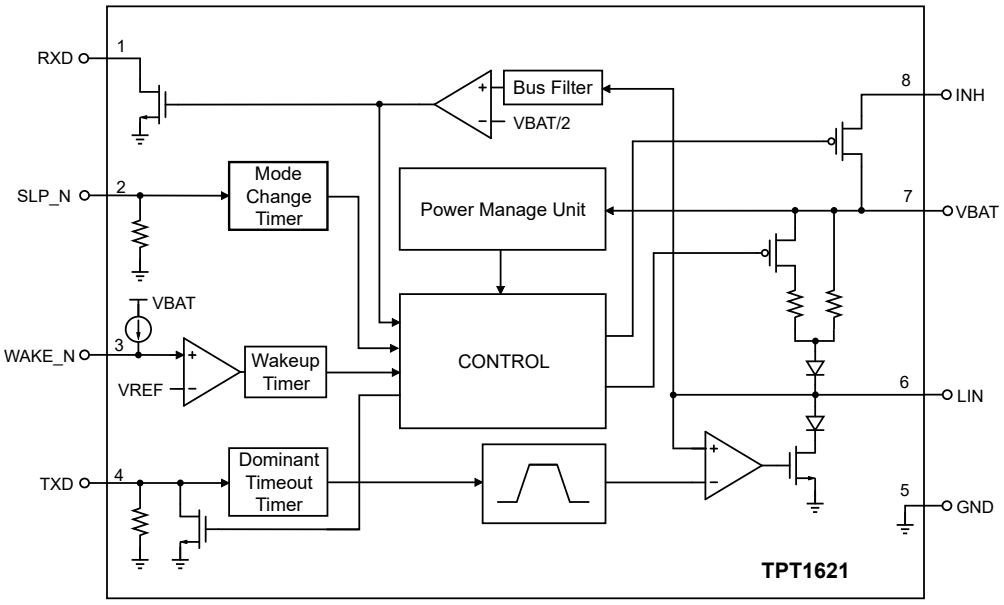


Figure 4. Functional Block Diagram

Feature Description

Device Operating Modes

The device supports modes for Normal, Power-on, Standby, and Sleep. The figure below shows the state diagram.

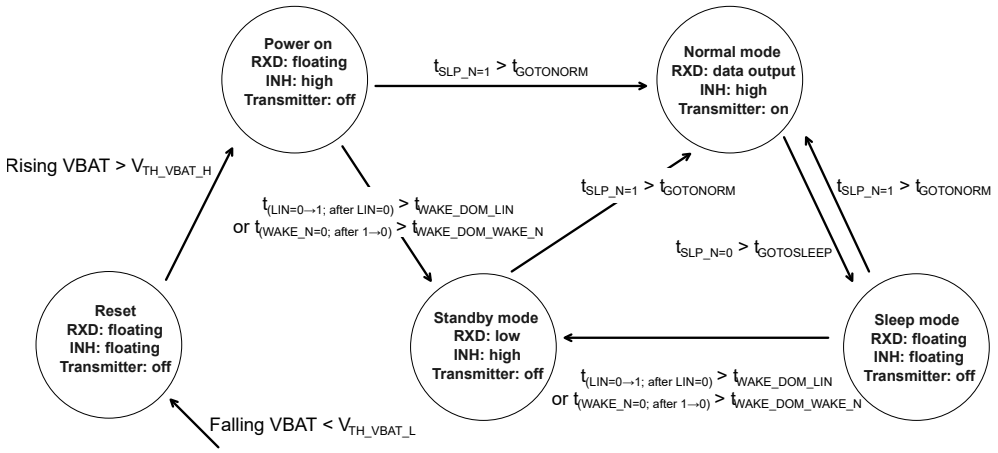


Figure 5. Operating Modes Diagram

Table 2. Function Table

Mode	SLP_N	TXD	RXD	INH	Transmitter	Comments
Normal	High	High: recessive state Low: dominant state	High: recessive state Low: dominant state	High	Normal	
Sleep	Low	Weak pull-down	Floating	Floating	Off	No wake-up event detected
Standby	Low	Weak pull-down if remote wake-up; strong pull-down if local wake-up	Low	High	Off	Wake-up event detected
Power-on	Low	Weak pull-down	Floating	High	Off	

Normal Mode

In Normal mode, the device can transmit and receive data through the LIN bus line. The receiver detects the data stream at the LIN bus input pin and transfers it to the microcontroller via the RXD pin. On the bus, a HIGH level corresponds to a recessive state, while a LOW level represents a dominant state. The receiver incorporates a voltage-dependent threshold with hysteresis and an integrated filter to suppress noise on the bus.

The transmit data stream from the protocol controller at the TXD input is converted by the transmitter into a bus signal with optimized slew rate and wave shaping, aiming to minimize electromagnetic emissions (EME). The LIN bus output pin is pulled HIGH through an internal slave termination resistor. For master applications, an external resistor in series with a diode should be connected between pin INH or VBAT and pin LIN.

Sleep Mode

The device offers an energy-efficient mode known as the power-saving mode. Despite its extremely low current consumption, the device retains the capability to be remotely awakened via the LIN pin, locally awakened via the WAKE_N pin, or directly activated through the SLP_N pin. Input filters are incorporated at the receiver (LIN), WAKE_N pin, and SLP_N pin to prevent undesired wake-up events caused by automotive transients or electromagnetic interference (EMI).

To initiate Sleep mode from Normal mode, a falling edge on the SLP_N pin is required. To successfully enter Sleep mode (INH pin becomes floating), the sleep command (SLP_N pin set to LOW) must be sustained for a minimum duration of $t_{gotosleep}$.

During Sleep mode, the internal slave termination between the LIN and VBAT pins is disabled to minimize power dissipation if the LIN pin is short-circuited to ground. Only a weak pull-up is present between the LIN and VBAT pins.

Standby Mode

Whenever a local or remote wake-up occurs while the device is in Sleep mode, Standby mode is automatically activated. These wake-up events trigger the activation of pin INH and enable the slave termination resistor at the LIN pin. Consequently, the voltage regulator and microcontroller can be powered on due to the HIGH condition of the INH pin.

Standby mode is indicated by a low level on the RXD pin, which can serve as an interrupt for the microcontroller.

During Standby mode (with pin SLP_N still low), the state of the TXD pin (weak pull-down or strong pull-down) indicates the source of the wake-up: a weak pull-down for a remote wake-up request and a strong pull-down for a local wake-up request.

Wake-up

When VBAT voltage exceeds the undervoltage threshold voltage, the device transitions into Power-on mode. In this mode, despite being powered up and INH being high, both the transmitter and receiver remain inactive. If SLP_N is HIGH for a duration greater than $t_{GOTONORM}$, the device enters Normal mode.

To wake up a device that is in Sleep mode, the device supports three wake-up methods:

Remote wake-up through the LIN bus by transmitting a dominant bus state sustained for a duration of at least $t_{WAKE_DOM_LIN}$ then followed by a rising edge.

Local wake-up is achieved by a falling edge signal at the WAKE_N pin and is sustained low for a duration of at least $t_{WAKE_DOM_WAKE_N}$. This transition triggers the wake-up event and brings the device out of Sleep mode.

Mode change by setting the SLP_N pin to a HIGH level. This change in pin state signals the device to exit Sleep mode and enter Normal mode.

Wake-up Source Recognition

The device is capable of distinguishing between a local wake-up request, initiated on pin WAKE_N, and a remote wake-up request through a dominant bus state. A local wake-up request activates the wake-up source flag, which can be accessed on pin TXD during Standby mode. If an external pull-up resistor is connected to pin TXD, a HIGH level indicates a remote wake-up request (with a weak pull-down at pin TXD), while a LOW level indicates a local wake-up request (with a strong pull-down at pin TXD, considerably stronger than the external pull-up resistor).

Both the wake-up request flag (indicated on pin RXD) and the wake-up source flag (indicated on pin TXD) reset immediately after the MCU sets pin SLP_N to a HIGH state.

Protection Features

TXD Dominant Time-out

The device detects TXD dominant time-out and prevents a permanent low on the TXD pin from driving the LIN bus into permanent dominant blocking the LIN bus network. If the TXD remains low for longer than $t_{TO_DOM_TXD}$, the transmitter is disabled until the fault flag has been cleared.

Under-voltage Lockout (UVLO)

The device integrates an under-voltage lockout (UVLO) circuit that keeps the device in a protected state whenever the supply voltage falls below $V_{TH_VBAT_L}$, and releases the lockout only after the supply voltage rises above $V_{TH_VBAT_H}$.

Over-Temperature Protection (OTP)

The output drivers are protected against over-temperature conditions. If the virtual junction temperature exceeds the shutdown junction temperature T_{J_SD}, the output drivers are disabled. Once the virtual junction temperature falls below $T_{J_SD} - T_{J_SD_HYS}$, TXD drivers are re-enabled. While this fault condition persists, the transceiver stays in normal mode. The on-chip LIN bus pull-up termination is kept enabled, and both the LIN receiver and the RXD pin remain active to mirror LIN bus data.

Fail-safe Features

An internal pull-down to GND on the TXD pin to establish a predetermined level in case the TXD pin is disconnected.

An internal pull-down to GND on the SLP_N pin to establish a predetermined level in case the SLP_N pin is disconnected.

The RXD pin is set to floating when the VBAT pin is unpowered.

The current limit is applied to the LIN transmitter output to protect the LIN bus from short circuits to VBAT or GND.

VBAT and GND loss will not impact the LIN bus or the MCU. No reverse current flows from the bus into the LIN pin. The internal integrated LIN slave termination resistor maintains the current path from VBAT to LIN. Disconnecting the LIN transceiver from the power supply does not affect the LIN bus.

Application and Implementation

Note

Information in the following application sections is not part of the 3PEAK's component specification and 3PEAK does not warrant its accuracy or completeness. 3PEAK's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

Typical Application

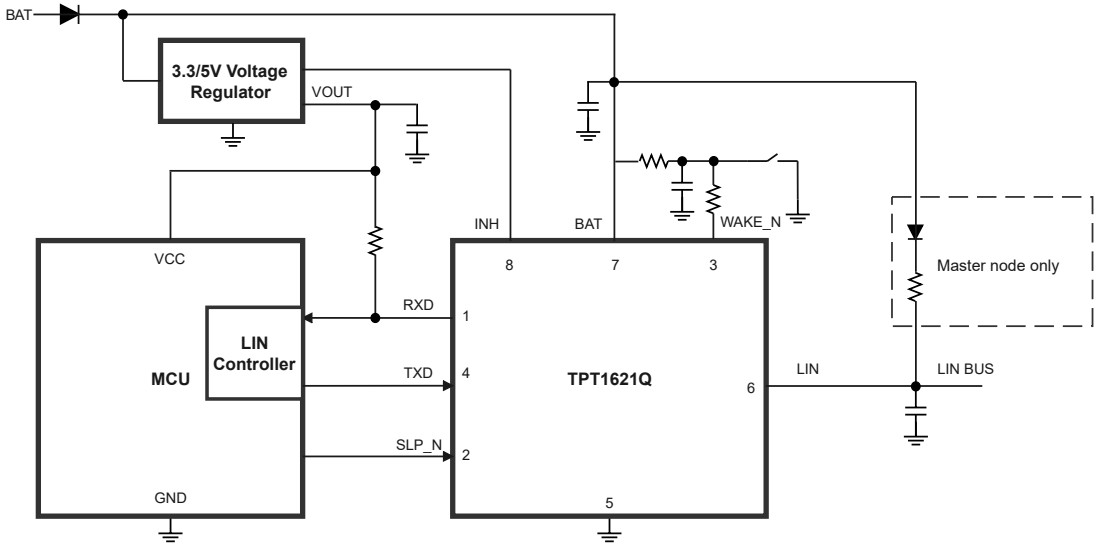
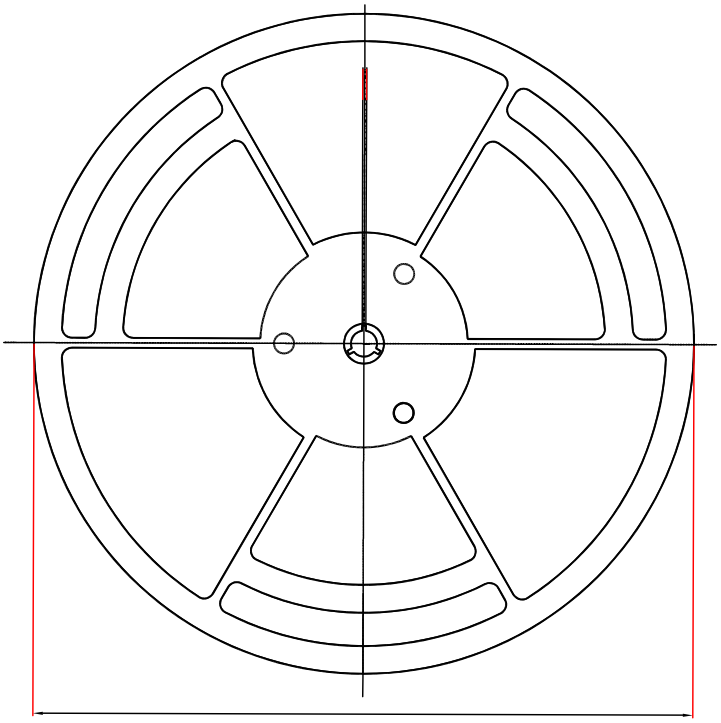
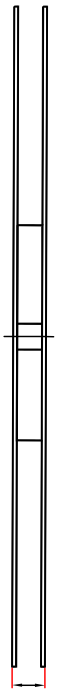
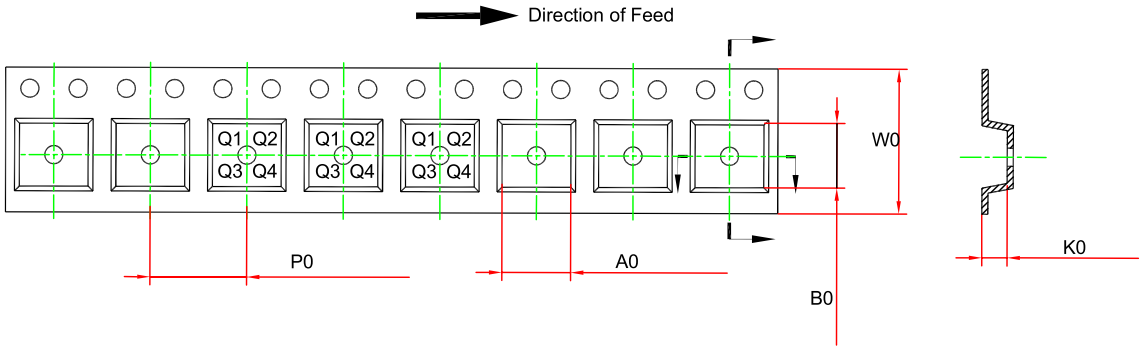


Figure 6. Typical Application Circuit

Tape and Reel Information





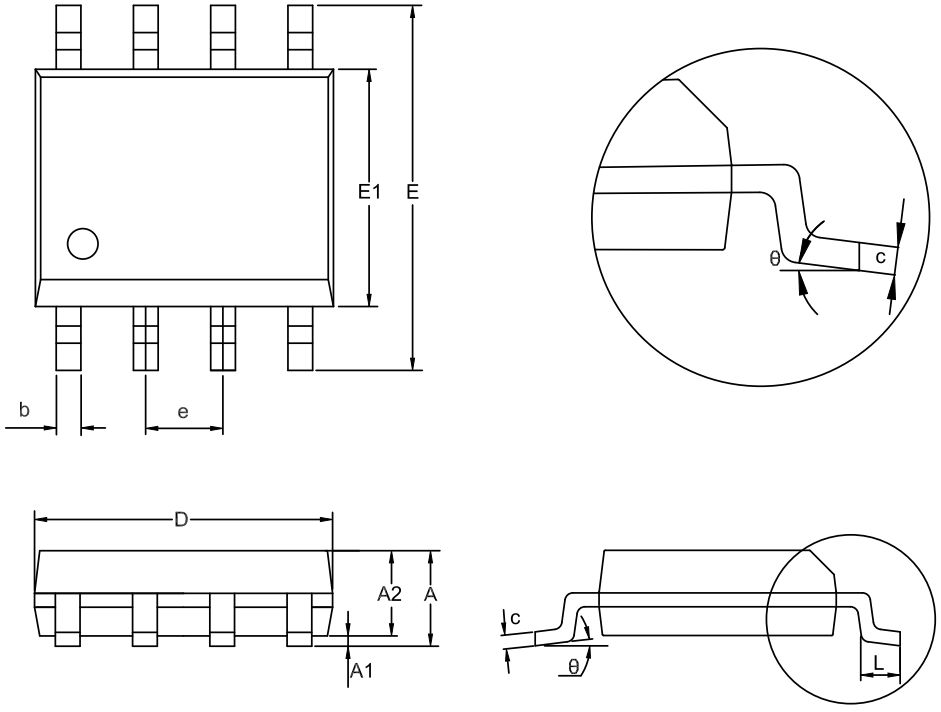


Order Number	Package	D1 (mm)	A0 (mm)	K0 (mm)	W0 (mm)	W1 (mm)	B0 (mm)	P0 (mm)	Pin1 Quadrant
TPT1621Q-SO1R-S	SOP8	330	6.5	2	12	17.6	5.4	8	Q1
TPT1621Q-DFCR-S	DFN3X3-8	330	3.3	1.1	12	17.6	3.3	8	Q1

Package Outline Dimensions

SOP8

Package Outline Dimensions SO1(SOP-8-A)



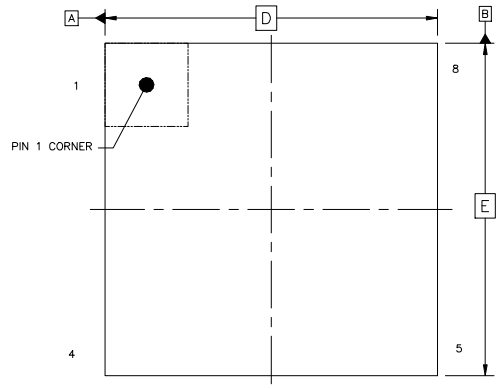
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	1.350	1.750	0.053	0.069
A1	0.050	0.250	0.002	0.010
A2	1.250	1.550	0.049	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.700	5.100	0.185	0.201
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
e	1.270 BSC		0.050 BSC	
L	0.400	1.000	0.016	0.039
θ	0	8°	0	8°

NOTES

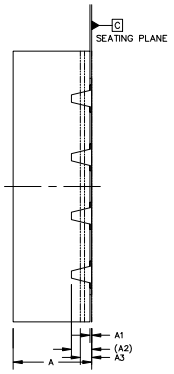
1. Do not include mold flash or protrusion.
2. This drawing is subject to change without notice.

DFN3X3-8

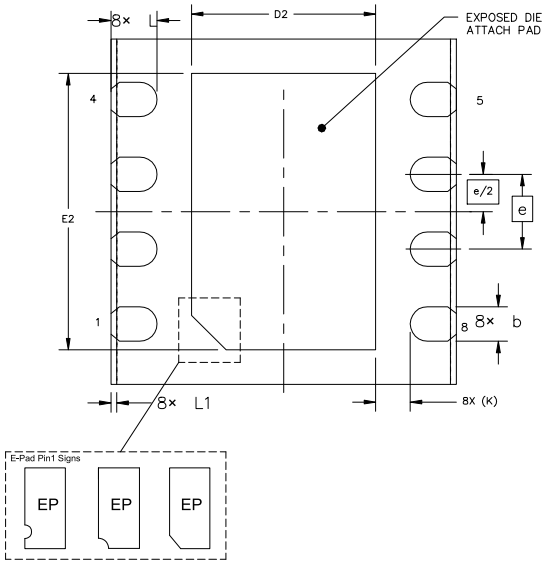
Package Outline Dimensions DFC(DFN3X3-8-WET-H)



TOP VIEW



SIDE VIEW



BOTTOM VIEW

NOTES

1. Do not include mold flash or protrusion.
2. This drawing is subject to change without notice.
3. The many types of E-pad Pin1 signs may appear in the product.

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	0.800	0.900	0.031	0.035
A1	0.000	0.050	0.000	0.002
A2	0.150	0.250	0.006	0.010
A3	0.080	0.180	0.003	0.007
D	2.900	3.100	0.114	0.122
D2	1.500	1.700	0.059	0.067
E	2.900	3.100	0.114	0.122
b	0.250	0.350	0.010	0.014
E2	2.300	2.500	0.091	0.098
e	0.650 BSC		0.026 BSC	
L	0.350	0.450	0.014	0.018
L1	0.010	0.090	0.0004	0.004
K	0.300 REF		0.012 REF	

Order Information

Order Number	Operating Temperature Range	Package	Marking Information	MSL	Transport Media, Quantity	Eco Plan
TPT1621Q-SO1R-S	−40 to 125°C	SOP8	T1621Q	1	Tape and Reel, 4000	Green
TPT1621Q-DFCR-S	−40 to 125°C	DFN3X3-8	T1621Q	1	Tape and Reel, 4000	Green

Green: 3PEAK defines "Green" to mean RoHS compatible and free of halogen substances.

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